

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







XPT IGBT

tentative

650 V V_{CES}

255A

V_{CE(sat)} = 1.6V

Single IGBT

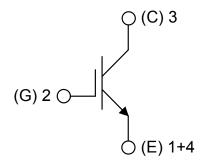
Part number

IXA2201650NA



Backside: isolated





Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
- short circuit rated for 10 µsec.
- very low gate charge
- low EMI
- square RBSOA @ 2x Ic
- Thin wafer technology combined with the XPT design results in a competitive low VCE(sat)

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipmentSwitched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outlineRoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Either emitter terminal can be used as main or Kelvin emitter





tentative

IGBT					1	Ratings	;	
Symbol	Definition		Conditions		min.	typ.	max.	Unit
V _{CES}	collector emitter voltage			$T_{VJ} = 25^{\circ}C$			650	V
V _{GES}	max. DC gate voltage						±20	V
V_{GEM}	max. transient gate emitter voltage						±30	V
I _{C25}	collector current			$T_{\rm C} = 25^{\circ} C$			255	Α
I _{C80}				$T_c = 80^{\circ}C$			156	Α
P _{tot}	total power dissipation	=		$T_{c} = 25^{\circ}C$			625	W
V _{CE(sat)}	collector emitter saturation voltage		I _C = 200A; V _{GE} = 15 V	$T_{VJ} = 25^{\circ}C$		1.6	1.8	V
				$T_{VJ} = 125^{\circ}C$		1.9		V
$V_{GE(th)}$	gate emitter threshold voltage		$I_{C} = 3.2 \text{mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}C$	4	4.8	5.5	V
I _{CES}	collector emitter leakage current		$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}C$			0.1	mΑ
				$T_{VJ} = 125^{\circ}C$		0.1		mΑ
I _{GES}	gate emitter leakage current		$V_{GE} = \pm 20 \text{ V}$				500	nA
Q _{G(on)}	total gate charge		V_{CE} = 300 V; V_{GE} = 15 V; I_{C} =	200 A		280		nC
t _{d(on)}	turn-on delay time	$\overline{}$				30		ns
t _r	current rise time		Part of a fact	T 40500		50		ns
$t_{d(off)}$	turn-off delay time		inductive load	$T_{VJ} = 125^{\circ}C$		100		ns
t _f	current fall time	٦	$V_{CE} = 300 \text{ V}; I_{C} = 200 \text{ A}$			40		ns
E _{on}	turn-on energy per pulse		$V_{GE} = \pm 15 \text{ V}; R_G = 3.9 \Omega$			2		mJ
E_{off}	turn-off energy per pulse	ノ				7.6		mJ
RBSOA	reverse bias safe operating area	7	$V_{GE} = \pm 15 \text{ V}; R_{G} = 3.9 \Omega$	T _{VJ} = 125°C				
I _{CM}			$V_{CEmax} = 650 V$				400	Α
SCSOA	short circuit safe operating area	7	V _{CEmax} = 650 V					
tsc	short circuit duration	}	$V_{CE} = 360 \text{ V}; V_{GE} = \pm 15 \text{ V}$	$T_{VJ} = 125^{\circ}C$			10	μs
I _{sc}	short circuit current	J	R_G = 3.9 Ω ; non-repetitive			800		Α
R _{thJC}	thermal resistance junction to case	-					0.2	K/W
R _{thCH}	thermal resistance case to heatsink					0.10		K/W

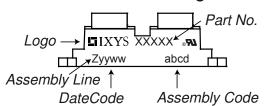


tentative

Package SOT-227B (minibloc)				Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal 1)					150	Α
T _{VJ}	virtual junction temperature)			-40		150	°C
Top	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{_{T}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	oroonago distanco on surfa	ace striking distance through air	terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage distance on suna	ice Striking distance through an	terminal to backside	8.6	6.8			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3000			V
		t = 1 minute			2500			V

¹⁾ l_{nusc} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.





Part description

I = IGBT
X = XPT IGBT
A = Gen 1 / std
220 = Current Rating [A]
I = Single IGBT

650 = Reverse Voltage [V] NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA220I650NA	IXA220I650NA	Tube	10	514555

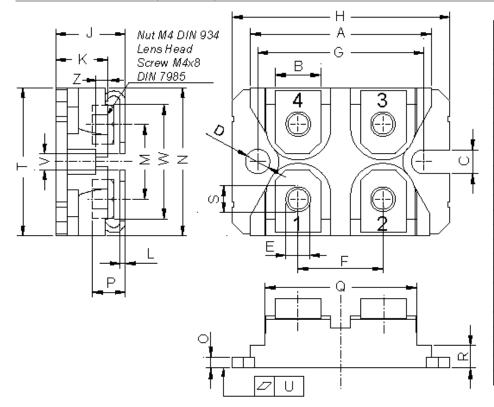
Equiva	alent Circuits for Simulation	* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$)[R _o]-	IGBT	
V _{0 max}	threshold voltage	1.1	V
R _{0 max}	slope resistance *	5.3	$m\Omega$





tentative

Outlines SOT-227B (minibloc)



Dim.	Millir	neter	Inches		
DIM.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	

